	Hits	Search Text	DBs
2	134	((substrate or wafer or platen) same (control$4 or regulat$4) same dissolv$4 same develop$4 same thickness same (resist or photoresist))	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB
3	199	((substrate or wafer or platen) same (control$4 or regulat$4) same (distribut$4 or spray$4 or nozzle) same develop$4 same (resist or photoresist or photosensitive)) and (dissolv$4 or solubiliz$4)	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB
4	155	((substrate or wafer or platen) same (control$4 or regulat$4) same (distribut$4 or spray$4 or nozzle) same develop$4 same (resist or photoresist or photosensitive)) and (dissolv$4 or solubiliz$4) and ((heat$4 or bak$4 or thermal$4) same (resist or photoresist))	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB
5	17	((substrate or wafer or platen) same (control$4 or regulat$4) same (distribut$4 or spray$4 or nozzle) same develop$4 same (resist or photoresist or photosensitive)) and (dissolv$4 or solubiliz$4) and ((heat$4 or bak$4 or thermal$4) same (resist or photoresist)) and (first near9 nozzle) and (second near9 nozzle) and (nozzle same (driv$4 or moveable or mov$4))	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
6	14	118/52.ccls. and ((resist or photoresist or resin) near16 (coat$4 or layer or film or form$4) near34 (nozzle)) and ((distribut$4 or spread$4 or divert$4 or spray$4) near26 (nozzle) near19 (resist or photoresist or resin$4) near36 (develop$4))	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB
7	3	118/52.ccls. and ((resist or photoresist or resin) near34 (nozzle)) and ((distribut$4 or spread$4 or divert$4 or spray$4) near26 (nozzle) near19 (develop$4)) and (dissolv$4 or solubiliz$4) and ((expos$4 or illuminat$4 or irradiat$4 or project$4) near12 (unit or system or chamber)) and ((heat$4 or bak$4 or thermal) near16 (interface or unit or chamber or system or subset))	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB
8	1414	118/52.ccls.	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB
9	36	((resist or photoresist or resin) near34 (nozzle)) and ((distribut$4 or spread$4 or divert$4 or spray$4) near26 (nozzle) near19 (develop$4)) and (dissolv$4 or solubiliz$4) and ((expos$4 or illuminat$4 or irradiat$4 or project$4) near12 (unit or system or chamber)) and ((heat$4 or bak$4 or thermal) near16 (interface or unit or chamber or system or subset))	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
10	113	((resist or photoresist or resin) near26 (nozzle)) and (dissolv$4 or solubiliz$4) and ((expos$4 or illuminat$4 or irradiat$4 or project$4) near12 (unit or system or chamber)) and ((heat$4 or bak$4 or thermal) near16 (interface or unit or chamber or system or subset)) and (nozzle same first same second) and (first near16 (resist or photoresist)) and (second near16 (resist or photoresist))	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB
11	36	((resist or photoresist or resin) near34 (nozzle)) and ((distribut$4 or spread$4 or divert$4 or spray$4) near26 (nozzle) near19 (develop$4)) and (dissolv$4 or solubiliz$4) and ((expos$4 or illuminat$4 or irradiat$4 or project$4) near12 (unit or system or chamber)) and ((heat$4 or bak$4 or thermal) near16 (interface or unit or chamber or system or subset))	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB
12	104	S10 NOT S11	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
13	31	((resist or photoresist or resin) near26 (nozzle)) and (dissolv$4 or solubiliz$4) and ((expos$4 or illuminat$4 or irradiat$4 or project$4) near12 (unit or system or chamber)) and ((heat$4 or bak$4 or thermal) near16 (interface or unit or chamber or system or subset)) and (nozzle same first same second) and (first near6 (resist or photoresist)) and (second near6 (resist or photoresist)) and (heat$4 near16 (top or upper or bottom or stage or lower or hold$4) near16 (substrate or wafer))	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB
14	20	S12 and (heat$4 same (top or upper) same (bottom or lower or (sustrate near5 holder) or hold$4 or stage) same (resist or photoresist) same (substrate or wafer))	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
15	5	((resist or photoresist or resin) near26 (nozzle)) and (dissolv$4 or solubiliz$4) and ((expos$4 or illuminat$4 or irradiat$4 or project$4) near12 (unit or system or chamber)) and ((heat$4 or bak$4 or thermal) near16 (interface or unit or chamber or system or subset)) and (nozzle same first same second) and (first near6 (resist or photoresist)) and (second near6 (resist or photoresist)) and (heat$4 near16 (top or upper or bottom or stage or lower or hold$4) near16 (substrate or wafer)) and (first near16 (expos$4 or illuminat$4 or irradiat$4))	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB
16	28	((resist or photoresist or resin) near26 (nozzle)) and (dissolv$4 or solubiliz$4) and ((expos$4 or illuminat$4 or irradiat$4 or project$4) near12 (unit or system or chamber)) and ((heat$4 or bak$4 or thermal) near16 (interface or unit or chamber or system or subset)) and (nozzle same first same second) and (first near6 (resist or photoresist)) and (second near6 (resist or photoresist)) and (first near16 (expos$4 or illuminat$4 or irradiat$4)) and (second near9 (expos$4 or irradiat$4 or illuminat$4))	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
17	4	((substrate or wafer or platen) same (resist or photoresist or resin) same (coat$4 or spray$3 or deposit$4 or form$3) same nozzle) and ((resist or photoresist or resin$4) same (control$4 or regulat$4 or monitor$4) same (distribut$4 or spray$4 or nozzle or spread$4 or apply$4) same develop$4 same (dissolv$4 or solubiliz$4) same thickness)	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB
18	26	((substrate or wafer or platen) same (resist or photoresist or resin) same (coat$4 or spray$3 or deposit$4 or form$3)) and (((resist or photoresist or resin$4) near9 (layer or film or layer or coat$4)) same (control$4 or regulat$4) same (distribut$4 or spray$4 or nozzle or spread$4 or apply$4) same develop$4 same (dissolv$4 or solubiliz$4) same thickness)	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB
19	26	((substrate or wafer or platen) same (resist or photoresist or resin) same (coat$4 or spray$3 or deposit$4 or form$3)) and (((resist or photoresist or resin$4) near9 (layer or film or layer or coat$4)) same (control$4 or regulat$4) same (distribut$4 or spray$4 or nozzle or spread$4 or apply$4) same develop$4 same (dissolv$4 or solubiliz$4) same thickness)	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
20	10	((substrate or wafer or platen) same (resist or photoresist or resin) same (coat$4 or spray$3 or deposit$4 or form$3) same (system or apparatus or unit)) and ((resist or photoresist or resin$4) same (control$4 or regulat$4) same (distribut$4 or spray$4 or nozzle or spread$4 or apply$4) same develop$4 same (dissolv$5 or solubil$6) same thickness)	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB
21	140	((resist or photoresist or resin) near34 (nozzle or spray)) and ((dissolv$4 or solubiliz$4 or develop$4) near20 (unit or interface or system)) and ((expos$4 or illuminat$4 or irradiat$4 or project$4) near12 (unit or system or chamber)) and ((heat$4 or bak$4 or thermal) near16 (interface or unit or chamber or system or subset)) and (first near3 (expos$4 or irradiat$4 or illuminat$4)) and ((double or second) near4 (expos$4 or irradiat$4 or illuminat$4))	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
22	4	((resist or photoresist or resin) near34 (nozzle or spray)) and ((dissolv$4 or solubiliz$4 or develop$4) near20 (unit or interface or system)) and ((expos$4 or illuminat$4 or irradiat$4 or project$4) near12 (unit or system or chamber)) and ((heat$4 or bak$4 or thermal) near16 (interface or unit or chamber or system or subset)) and (first near3 (expos$4 or irradiat$4 or illuminat$4)) and ((double or second) near4 (expos$4 or irradiat$4 or illuminat$4)) and ((temperature or heat$4 or bak$4) near16 (substrate or wafer or workpiece) near22 (resist or photoresist) near33 (stage or hold$4)) and (second near6 (temperature or heat$4 or bak$4))	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
23	66	((resist or photoresist or resin) near34 (nozzle or spray)) and ((dissolv$4 or solubiliz$4 or develop$4) near20 (unit or interface or system)) and ((expos$4 or illuminat$4 or irradiat$4 or project$4) near12 (unit or system or chamber)) and ((heat$4 or bak$4 or thermal) near16 (interface or unit or chamber or system or subset)) and (first near3 (expos$4 or irradiat$4 or illuminat$4)) and ((double or second) near4 (expos$4 or irradiat$4 or illuminat$4)) and ((temperature or heat$4 or bak$3) near16 (substrate or wafer or workpiece) near22 (resist or photoresist)) and (second near13 (temperature or heat$4 or bak$3)) and (first near12 (temperature or heat$4 or bak$3))	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB
24	2	((substrate or wafer or platen) same (resist or photoresist or resin) same (coat$4 or spray$3 or deposit$4 or form$3) same nozzle) and ((resist or photoresist or photocur$4 or resin$4) near16 nozzle near26 first near19 second) and (first near3 (resist or photoresist)) and ((second or dual or double) near3 (resist or photoresist)) and (first near6 (expos$4 or illuminat$4 or irradiat$4) near9 (energy or amount or intensit$3)) and (second near4 (expos$4 or irradiat$4 or illuminat$4) near10 (intensi$4 or amount or energy))	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
25	115	((substrate or wafer or platen) same (resist or photoresist or resin) same (coat$4 or spray$3 or deposit$4 or form$3) same nozzle) and ((resist or photoresist or photocur$4 or resin$4) near16 nozzle near26 first near19 second) and (first near3 (resist or photoresist)) and ((second or dual or double) near3 (resist or photoresist))	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB
26	143	((substrate or wafer or platen) same (resist or photoresist or resin)) and ((resist or photoresist or photocur$4 or resin$4) near16 nozzle) and (first near26 (liquid or resist or photoresist) near26 (nozzle or discharge)) and (second near22 (resist or photoresist or liquid) near26 (nozzle or discharge)) and ((first near3 (resist or photoresist)) same ((second or dual or double) near3 (resist or photoresist)))	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB
27	115	((substrate or wafer or platen) same (resist or photoresist or resin) same (coat$4 or spray$3 or deposit$4 or form$3) same nozzle) and ((resist or photoresist or photocur$4 or resin$4) near16 nozzle near26 first near19 second) and (first near3 (resist or photoresist)) and ((second or dual or double) near3 (resist or photoresist))	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
28	49	S26 NOT S27	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB
29	306	((substrate or wafer or platen) same (resist or photoresist or resin) same (coat$4 or spray$3 or deposit$4 or form$3) same nozzle) and ((resist or photoresist or photocur$4 or resin$4) near6 first near6 (top or second or dual)) and (first near3 (resist or photoresist)) and ((second or dual or double) near3 (resist or photoresist))	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB
30	204	S29 NOT S27	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB
31	172	S30 NOT S26	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
32	140	((resist or photoresist or resin) near34 (nozzle or spray)) and ((dissolv$4 or solubiliz$4 or develop$4) near20 (unit or interface or system)) and ((expos$4 or illuminat$4 or irradiat$4 or project$4) near12 (unit or system or chamber)) and ((heat$4 or bak$4 or thermal) near16 (interface or unit or chamber or system or subset)) and (first near3 (expos$4 or irradiat$4 or illuminat$4)) and ((double or second) near4 (expos$4 or irradiat$4 or illuminat$4))	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB
33	163	S31 NOT S32	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB
34	163	S33 and nozzle	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB
35	35	S33 and (nozzle same driv$4)	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB